DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

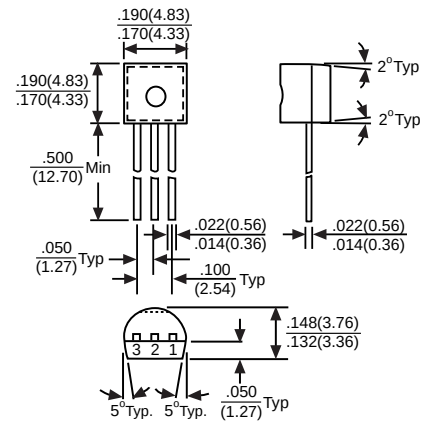
MPSA92M

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

Designed for use as a video output to drive color CRT, or as a dialer circuit in electronic telephone.

TO-92



Dimensions in inches and (millimeters)

Pinning

1 = Emitter
2 = Base
3 = Collector

Absolute Maximum Ratings (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Total Power Dissipation	P_D	625	mW
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-55 to +150	°C

Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Volatge	BV_{CBO}	-300	-	-	V	I_C=-100μA, I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-300	-	-	V	I_C=-1mA, I_B=0
Emitter-Base Breakdown Volatge	BV_{EBO}	-5	-	-	V	I_E=-10μA, I_C=0
Collector Cutoff Current	I_{CEO}	-	-	-5	μA	V_{CE}=-300V, I_B=0
Emitter Cutoff Current	I_{EBO}	-	-	-0.1	μA	V_{EB}=-3V, I_C=0
Collector-Emitter Saturation Voltage(1)	$V_{CE(sat)1}$	-	-0.15	-	V	I_C=-30mA, I_B=-1mA
	$V_{CE(sat)2}$	-	-	-0.7	V	I_C=-100mA, I_B=-10mA
Base-Emitter Saturation Voltage(1)	$V_{BE(sat)1}$	-	-	-0.9	V	I_C=-20mA, I_B=-2mA
	$V_{BE(sat)2}$	-	-	-1	V	I_C=-100mA, I_B=-10mA
DC Current Gain(1)	h_{FE1}	80	-	-	-	I_C=-10mA, V_{CE}=-10V
	h_{FE2}	80	-	-	-	I_C=-100mA, V_{CE}=-10V
	h_{FE3}	40	-	-	-	I_C=-200mA, V_{CE}=-10V
Transition Frequency	f_T	50	-	-	MHz	I_C=-10mA, V_{CE}=-20V, f=100MHz

(1)Pulse Test: Pulse Width ≦380μs, Duty Cycle ≦2%